



SEMICONDUCTOR

TECHNICAL DATA

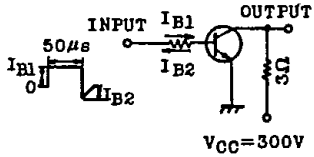
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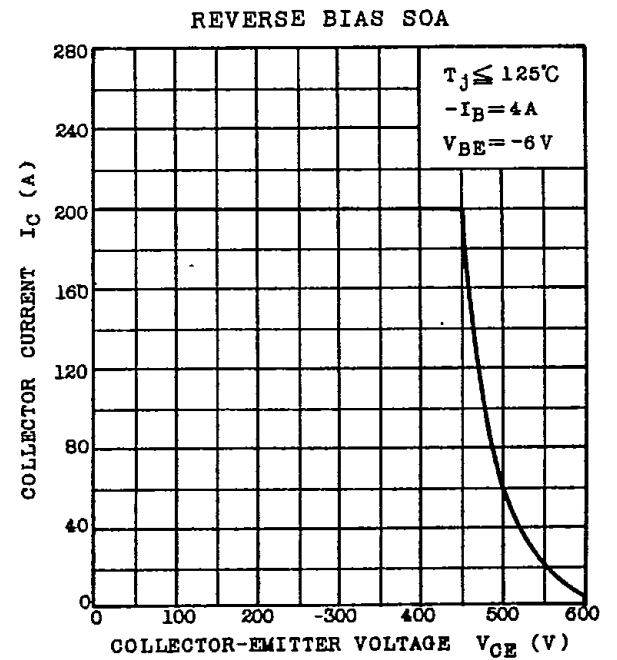
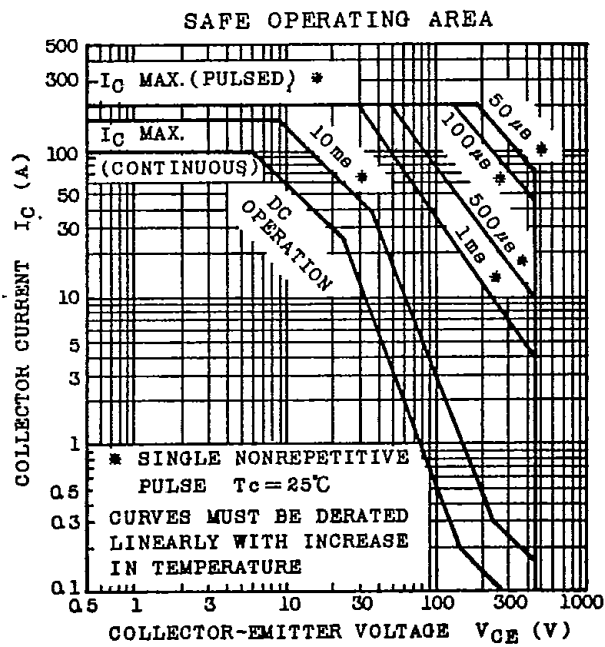
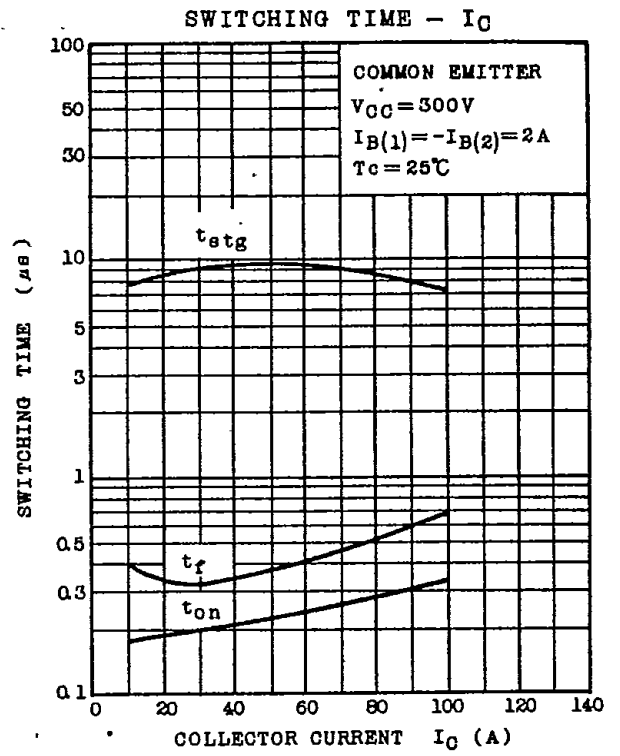
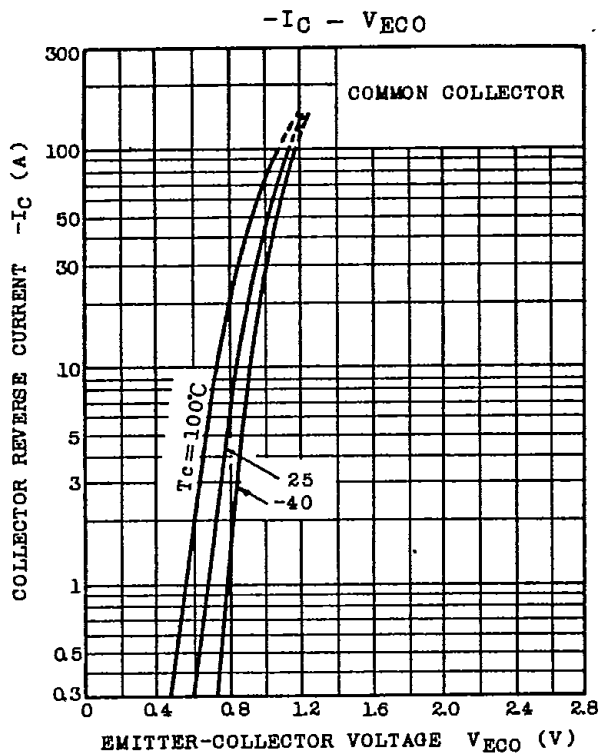
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MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		VCBO	600	V
Collector-Emitter Voltage		VCEO	600	V
Collector-Emitter Sustaining Voltage		VCEO(SUS)	450	V
Emitter-Base Voltage		VEBO	6	V
Collector Current	DC	IC	100	A
	1ms	IC	200	
	DC	-IC	100	
Base Current		IB	5	A
Collector Power Dissipation (Tc=25°C)		PC	600	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-40 ~ 125	°C
Isolation Voltage		VIsol	2500 (AC 1 Minute)	V
Screw Torque		-	30	kg·cm

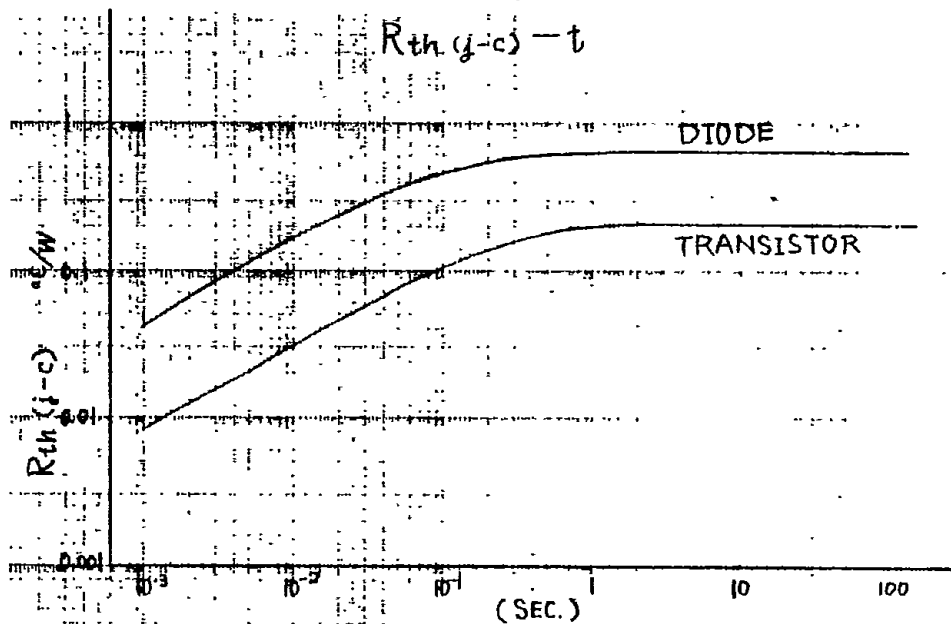
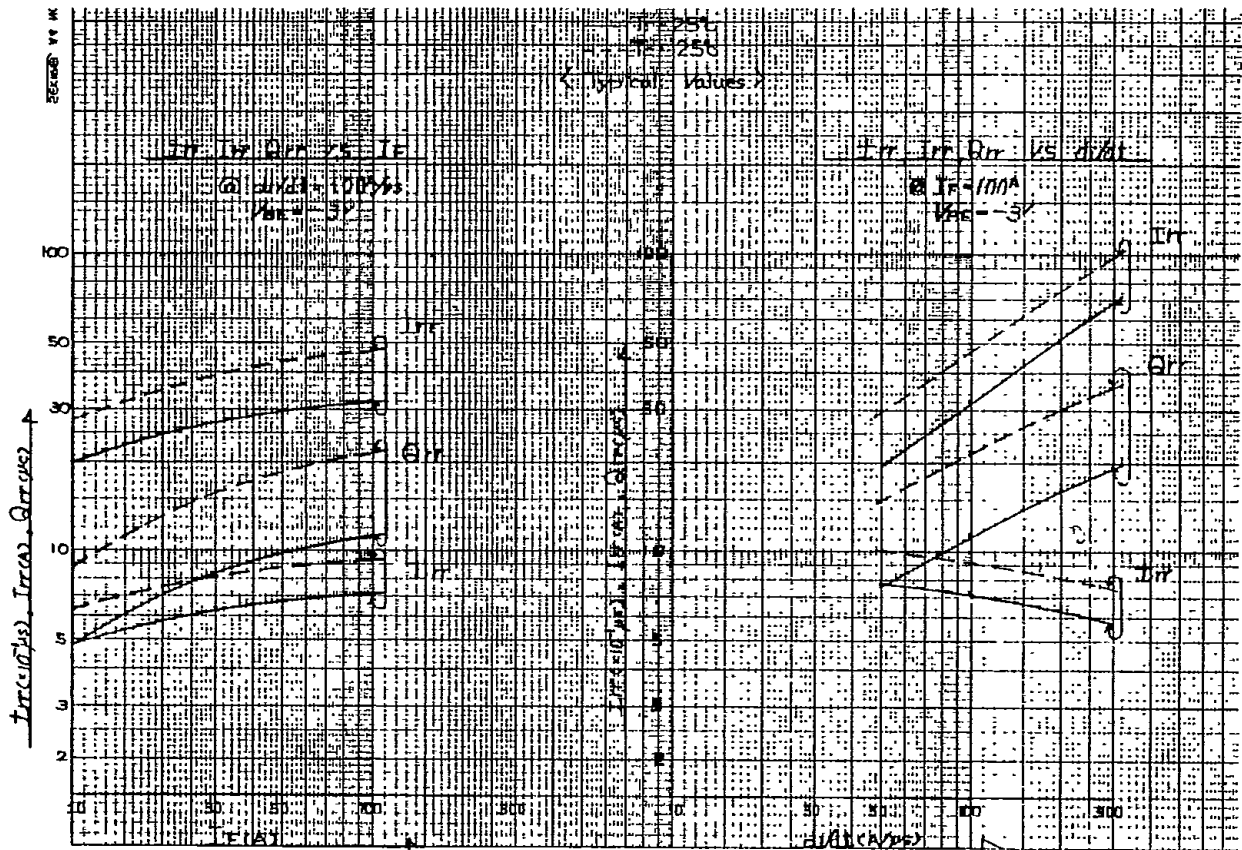
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	VCB=600V, IE=0	-	-	2.0	mA
Emitter Cut-off Current		IEBO	VEB=6V, IC=0	-	-	400	mA
Collector-Emitter Sustaining Voltage		VCEO(SUS)	IC=0.5A, L=40mH	450	-	-	V
DC Current Gain		hFE	VCE=5V, IC=100A	100	-	-	
Collector-Emitter Saturation Voltage		VCE(sat)	IC=100A, IB=2A	-	-	2.0	V
Base-Emitter Saturation Voltage		VBE(sat)		-	-	2.5	V
Emitter-Collector Voltage		VECO	IE=100A, IB=0	-	-	1.5	V
Reverse Recovery Time		trr	-IC=100A, VEB=3V VCE=300V	-	-	2.0	μs
Collector Output Capacitance		Cob	VCB=50V, IE=0 f=1MHz	-	1000	-	pF
Switching Time	Turn-on Time	ton		-	-	1.0	μs
	Storage Time	tstg		-	-	12	
	Fall Time	tf		-	-	2.0	
Thermal Resistance (Junction to Case)		Rth(j-c)	Transistor	-	-	0.208	°C/W
			Diode	-	-	0.65	



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